# High Current Surface Mount NPN Silicon Switching Transistor for Load Management in Portable Applications

## **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	30	Vdc
Collector-Base Voltage	$V_{CBO}$	50	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	1.0	Α
Collector Current – Peak	I <sub>CM</sub>	2.0	Α

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub> (Note 1)	310 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub> (Note 1)	403	°C/W
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub> (Note 2)	710 5.7	mW mW/°C
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub> (Note 2)	176	°C/W
Total Device Dissipation (Single Pulse < 10 sec.)	P <sub>Dsingle</sub>	575	mW
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

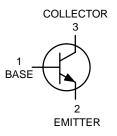
- 1. FR-4 @ Minimum Pad
- 2. FR-4 @ 1.0 X 1.0 inch Pad



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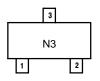
# 30 VOLTS 2.0 AMPS NPN TRANSISTOR





SOT-23 (TO-236) CASE 318-08 STYLE 6

#### **DEVICE MARKING**



N3 = Specific Device Code

## **ORDERING INFORMATION**

Device	Package	Shipping
MMBT489LT1	SOT-23	3000/Tape & Reel

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	ı
Collector – Emitter Breakdown Voltage $(I_C = 10 \text{ mAdc}, I_B = 0)$	V <sub>(BR)</sub> CEO	30	-	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 0.1 mAdc, I <sub>E</sub> = 0)	V <sub>(BR)</sub> CBO	50	-	Vdc
Emitter – Base Breakdown Voltage $(I_E = 0.1 \text{ mAdc}, I_C = 0)$	V <sub>(BR)EBO</sub>	5.0	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	І <sub>СВО</sub>	-	0.1	μAdc
Collector–Emitter Cutoff Current (V <sub>CES</sub> = 30 Vdc)	I <sub>CES</sub>	_	0.1	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 4.0 Vdc)	I <sub>EBO</sub>	-	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain (Note 1) $ (I_C = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}) $ $ (I_C = 0.5 \text{ A}, V_{CE} = 5.0 \text{ V}) $ $ (I_C = 1.0 \text{ A}, V_{CE} = 5.0 \text{ V}) $	h <sub>FE</sub>	300 300 200	- 900 -	
Collector–Emitter Saturation Voltage (Note 1) ( $I_C = 1.0 \text{ A}, I_B = 100 \text{ mA}$ ) ( $I_C = 0.5 \text{ A}, I_B = 50 \text{ mA}$ ) ( $I_C = 0.1 \text{ A}, I_B = 1.0 \text{ mA}$ )	V <sub>CE(sat)</sub>	- - -	0.200 0.125 0.075	V
Base – Emitter Saturation Voltage (Note 1) (I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 0.1 A)	V <sub>BE(sat)</sub>	-	1.1	V
Base – Emitter Turn–on Voltage (Note 1) (I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 2.0 V)	V <sub>BE(on)</sub>	-	1.1	V
Cutoff Frequency ( $I_C = 100 \text{ mA}$ , $V_{CE} = 5.0 \text{ V}$ , $f = 100 \text{ MHz}$	f⊤	100	-	MHz
Output Capacitance (f = 1.0 MHz)	C <sub>obo</sub>			pF

<sup>1.</sup> Pulsed Condition: Pulse Width = 300  $\mu sec$ , Duty Cycle  $\leq 2\%$ 

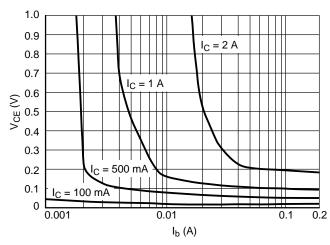
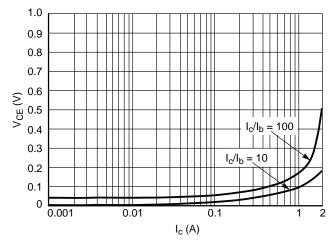


Figure 1. V<sub>CE</sub> versus I<sub>b</sub>



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Figure 2.  $V_{CE}$  versus  $I_{c}$ 

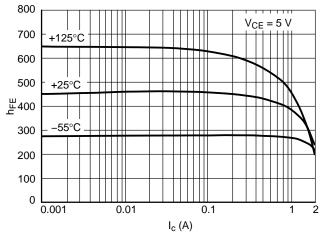


Figure 3. h<sub>FE</sub> versus I<sub>c</sub>

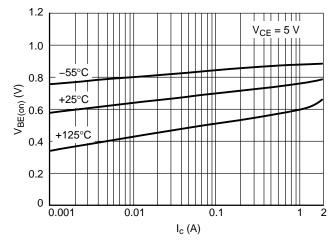


Figure 4. V<sub>BE(on)</sub> versus I<sub>c</sub>

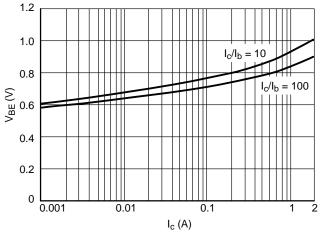


Figure 5.  $V_{BE(sat)}$  versus  $I_c$ 

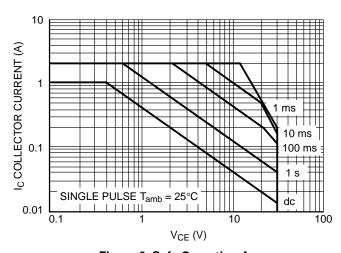


Figure 6. Safe Operating Area

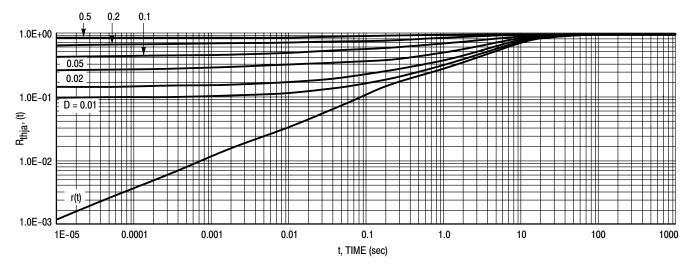
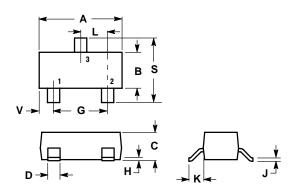


Figure 7. Normalized Thermal Response

#### **PACKAGE DIMENSIONS**

**SOT-23 (TO-236)** CASE 318-08 ISSUE AH



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
  Y14 5M 1982
- 2. CONTROLLING DIMENSION: INCH.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE
- 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
С	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
Н	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
٧	0.0177	0.0236	0.45	0.60

STYLE 6:

PIN 1. BASE

2. EMITTER3. COLLECTOR

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